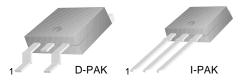


### KSH32/32C

### **General Purpose Amplifier Low Speed Switching Applications** D-PAK for Surface Mount Applications • Lead Formed for Surface Mount Application (No Suffix)

- Straight Lead (I-PAK, "- I" Suffix)
- Electrically Similar to Popular TIP32 and TIP32C



1.Base 2.Collector 3.Emitter

### **PNP Epitaxial Silicon Transistor**

### Absolute Maximum Ratings T<sub>C</sub>=25°C unless otherwise noted

Symbol	Parameter	Value	Units
$V_{CBO}$	Collector-Base Voltage : KSH32	- 40	V
	: KSH32C	- 100	V
V <sub>CEO</sub>	Collector-Emitter Voltage : KSH32	- 40	V
020	: KSH32C	- 100	V
V <sub>EBO</sub>	Emitter-Base Voltage	- 5	V
I <sub>C</sub>	Collector Current (DC)	- 3	Α
I <sub>CP</sub>	Collector Current (Pulse)	- 5	Α
I <sub>B</sub>	Base Current	- 1	Α
P <sub>C</sub>	Collector Dissipation (T <sub>C</sub> =25°C)	15	W
	Collector Dissipation (T <sub>a</sub> =25°C)	1.56	W
TJ	Junction Temperature	150	°C
T <sub>STG</sub>	Storage Temperature	- 65 ~ 150	°C

### Electrical Characteristics T<sub>C</sub>=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units
V <sub>CEO</sub> (sus)	* Collector-Emitter Sustaining Voltage				
	: KSH32	$I_C = -30 \text{mA}, I_B = 0$	-40		V
	: KSH32C		-100		V
I <sub>CEO</sub>	Collector Cut-off Current				
020	: KSH32	$V_{CE} = -40V, I_{B} = 0$		-50	μΑ
	: KSH32C	$V_{CE} = -60V, I_B = 0$		-50	μΑ
I <sub>CES</sub>	Collector Cut-off Current				
	: KSH32	$V_{CE} = -40V, V_{BE} = 0$		-20	μΑ
	: KSH32C	$V_{CE} = -100V, V_{BE} = 0$		-20	μΑ
I <sub>EBO</sub>	Emitter Cut-off Current	$V_{BE} = -5V, I_{C} = 0$		-1	mA
h <sub>FE</sub>	* DC Current Gain	V <sub>CE</sub> = - 4V, I <sub>C</sub> = - 1A	25		
		$V_{CE} = -4V, I_{C} = -3A$	10	50	
V <sub>CE</sub> (sat)	* Collector-Emitter Saturation Voltage	I <sub>C</sub> = - 3, I <sub>B</sub> = - 375mA		-1.2	V
V <sub>BE</sub> (on)	* Base-Emitter On Voltage	V <sub>CE</sub> = - 4A, I <sub>C</sub> = - 3A		-1.8	V
f <sub>T</sub>	Current Gain Bandwidth Product	V <sub>CE</sub> = -10V, I <sub>C</sub> = - 500mA	3		MHz

<sup>\*</sup> Pulse Test: PW≤300µs, Duty Cycle≤2%

# **Typical Characteristics**

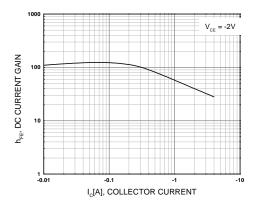


Figure 1. DC current Gain

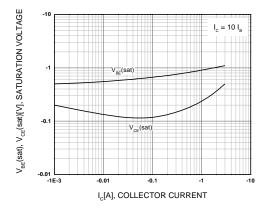


Figure 2. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

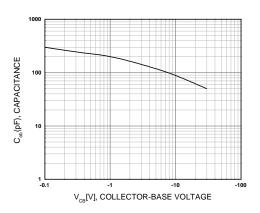


Figure 3. Collector Capacitance

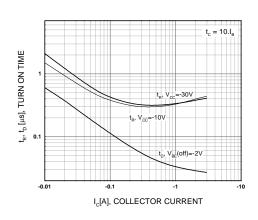


Figure 4. Turn On Time

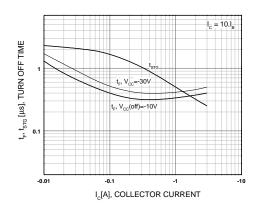


Figure 5. Turn Off Time

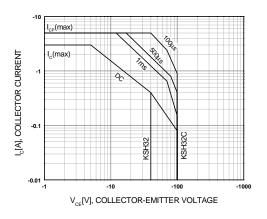


Figure 6. Safe Operating Area

# Typical Characteristics (Continued)

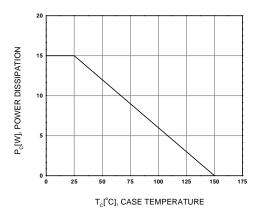
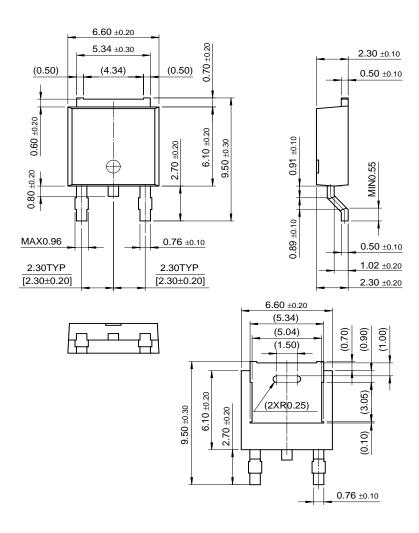


Figure 7. Power Derating

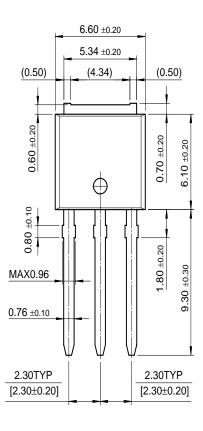
## **Package Dimensions**

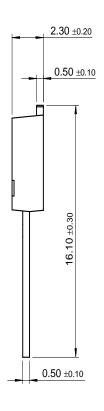
## D-PAK



## Package Dimensions (Continued)

## I-PAK







Dimensions in Millimeters

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CoolFET™	FASTr™	MicroFET™	PowerTrench <sup>®</sup>	SuperSOT™-6
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DOME™	GlobalOptoisolator™	MICROWIRE™	QS™	SyncFET™
EcoSPARK™	GTO™	MSX™	QT Optoelectronics™	TinyLogic™
E <sup>2</sup> CMOS™	HiSeC™	MSXPro™	Quiet Series™	TruTranslation™
EnSigna™	$I^2C^{TM}$	$OCX^{TM}$	RapidConfigure™	UHC™
Across the board. Around the world.™		OCXPro™	RapidConnect™	UltraFET <sup>®</sup>
The Power Franchise™		OPTOLOGIC <sup>®</sup>	SILENT SWITCHER®	VCX <sup>TM</sup>
Programmable Active Droop™		OPTOPLANAR™	SMART START™	

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